Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I	V_D =12V R_L =33Ω	- -	MAX.	50	
V		- -	MAX.	1	V
V	V_D = V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN	0.2 V	
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA
				90	
I_H	I_T =100mA		MAX.	50	mA
dV/dt	V_D=800V Gate Open T_j =125		MIN.	500	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j				

t_{on} mA CH0 TdARACTERIS.

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FIG.1: Maximum power dissipation versus RMS on-state current

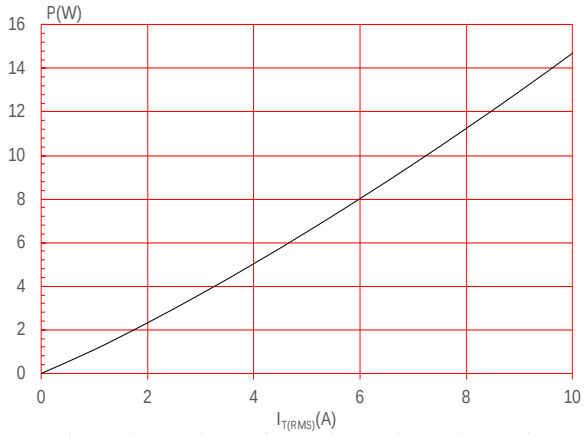


FIG.2: RMS on-state current versus case temperature

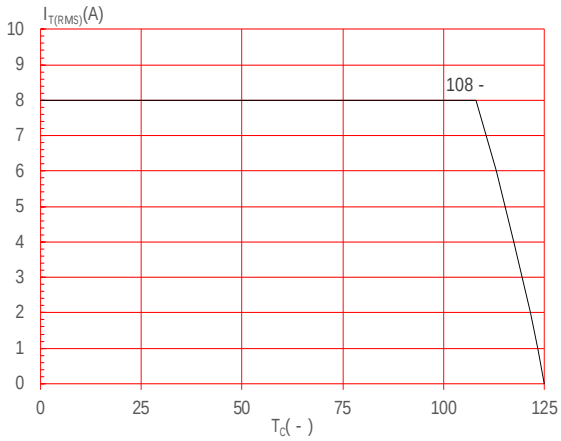


FIG.3: Surge peak on-state current versus number of cycles

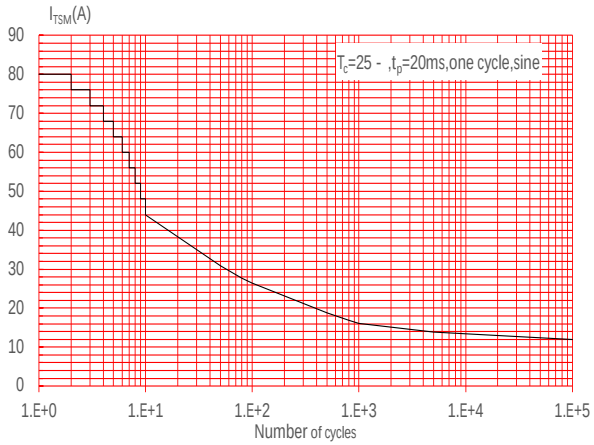


FIG.4: On-state characteristics

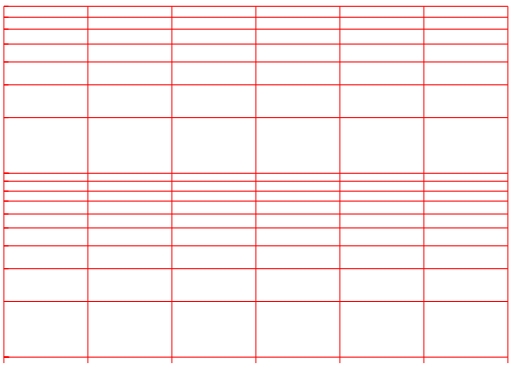
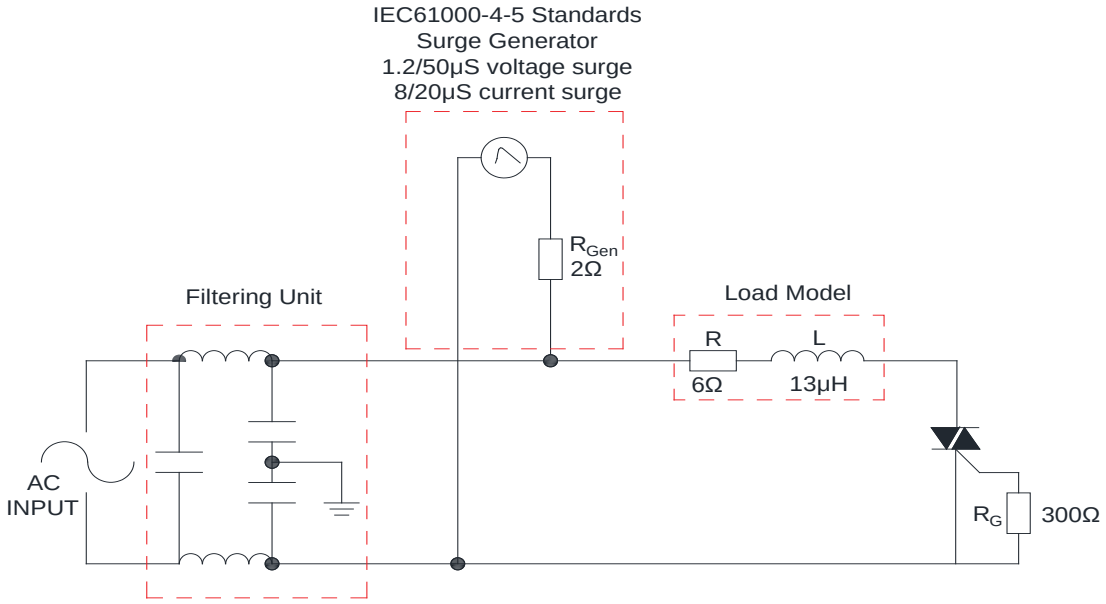


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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